





FIG.4

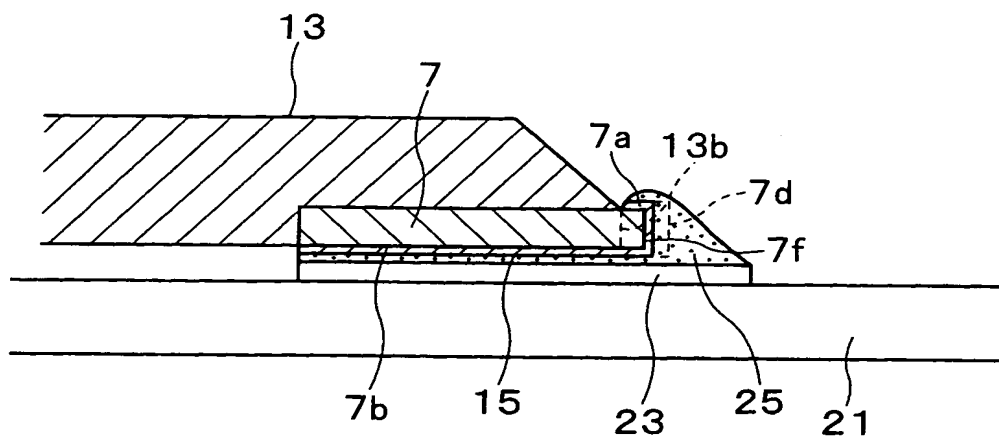
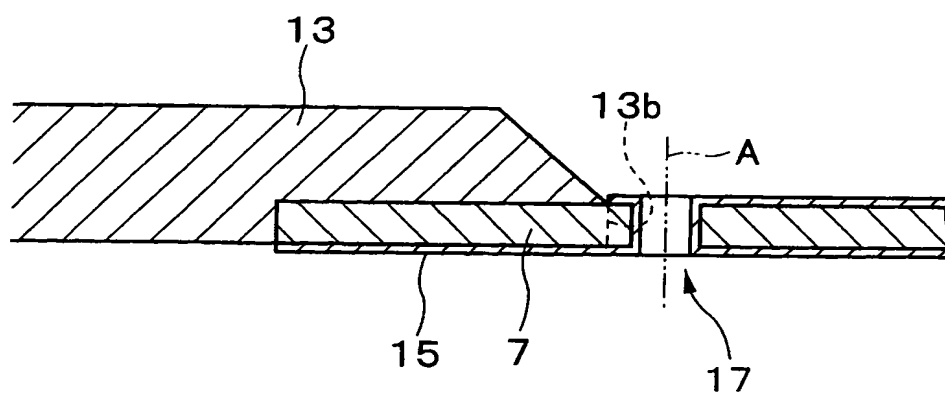


FIG.5



A cross-sectional view of a semiconductor device. It features a substrate 13 with a top surface 31. Four pillars 6 are formed on the surface. The first three pillars have a core 6a and a top layer 15. The fourth pillar has a core 6a, a top layer 15, and a side layer 6b. The side layer 6b is shown with a dashed line 6d and a dotted pattern 6f. The pillars are connected to a common layer 13.

FIG.8

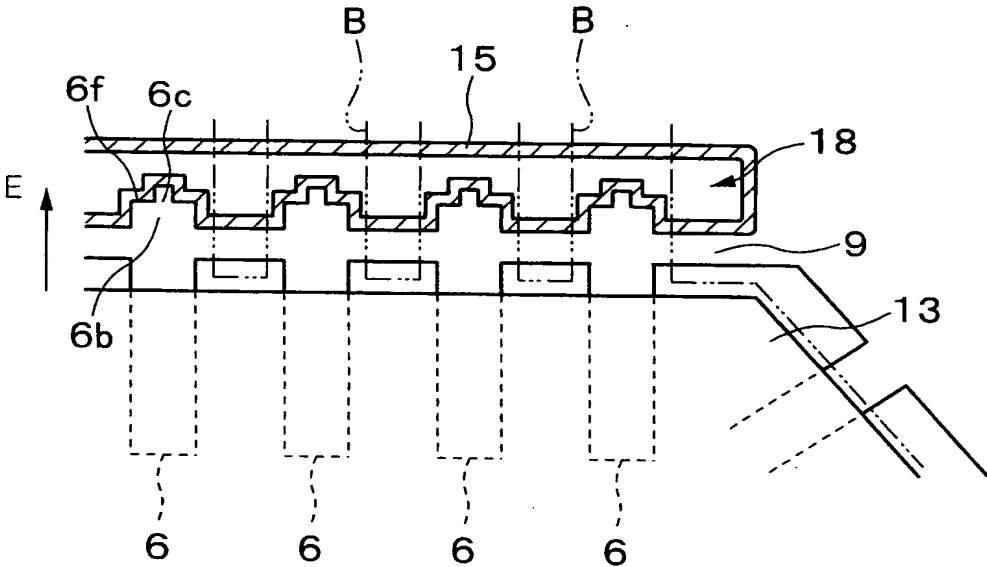


FIG.9

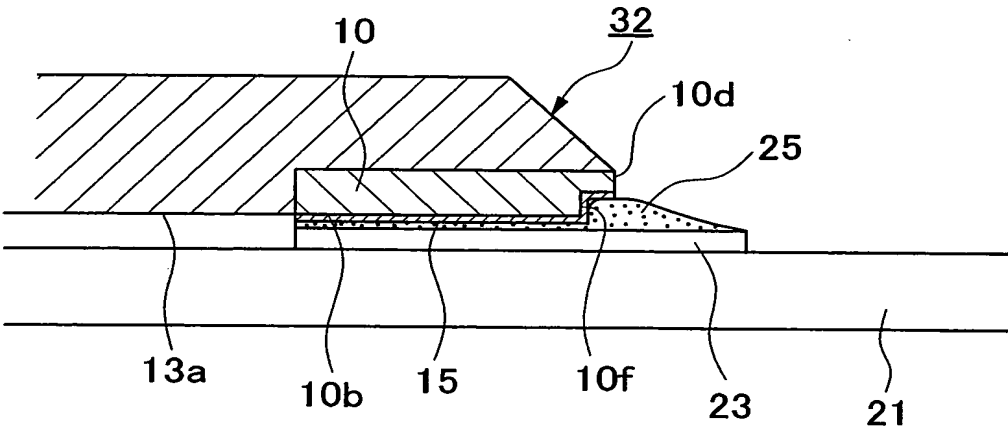


FIG.10

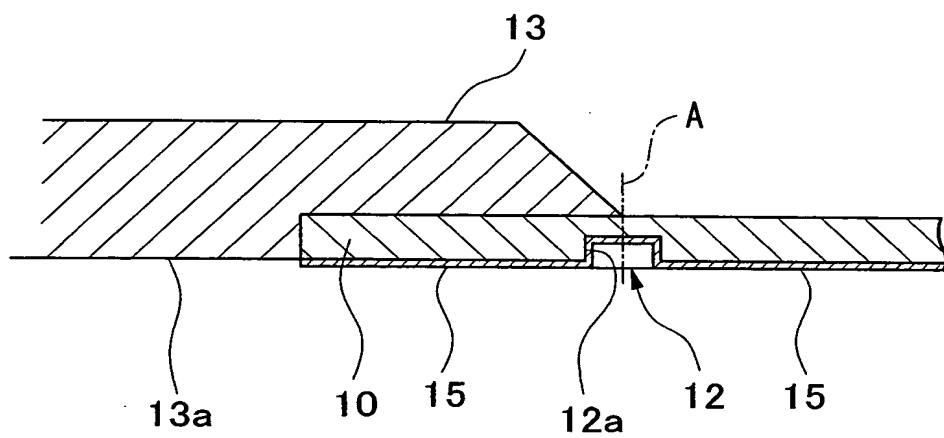


FIG.11

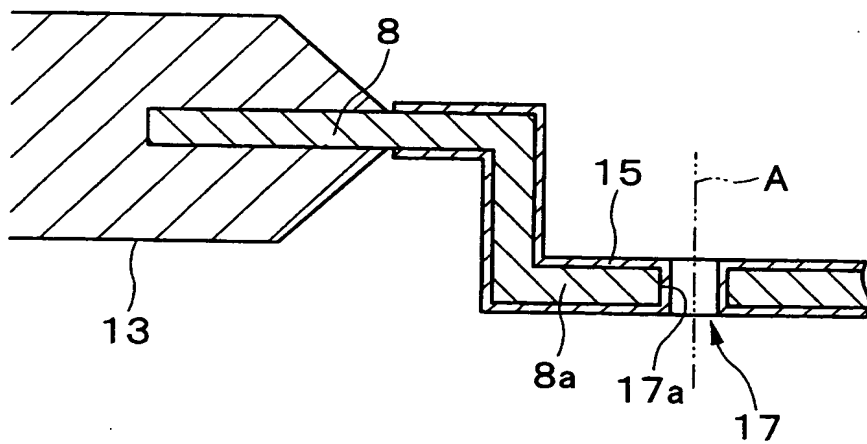


FIG.12

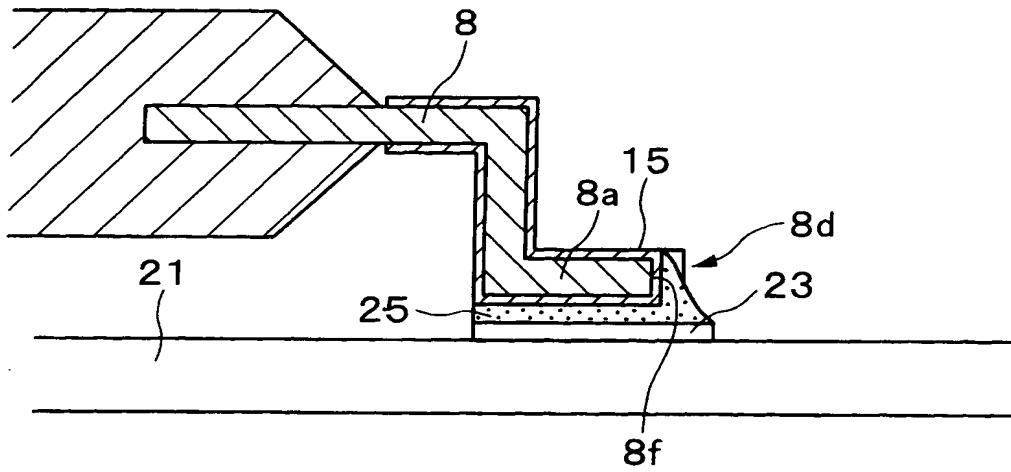


FIG.13

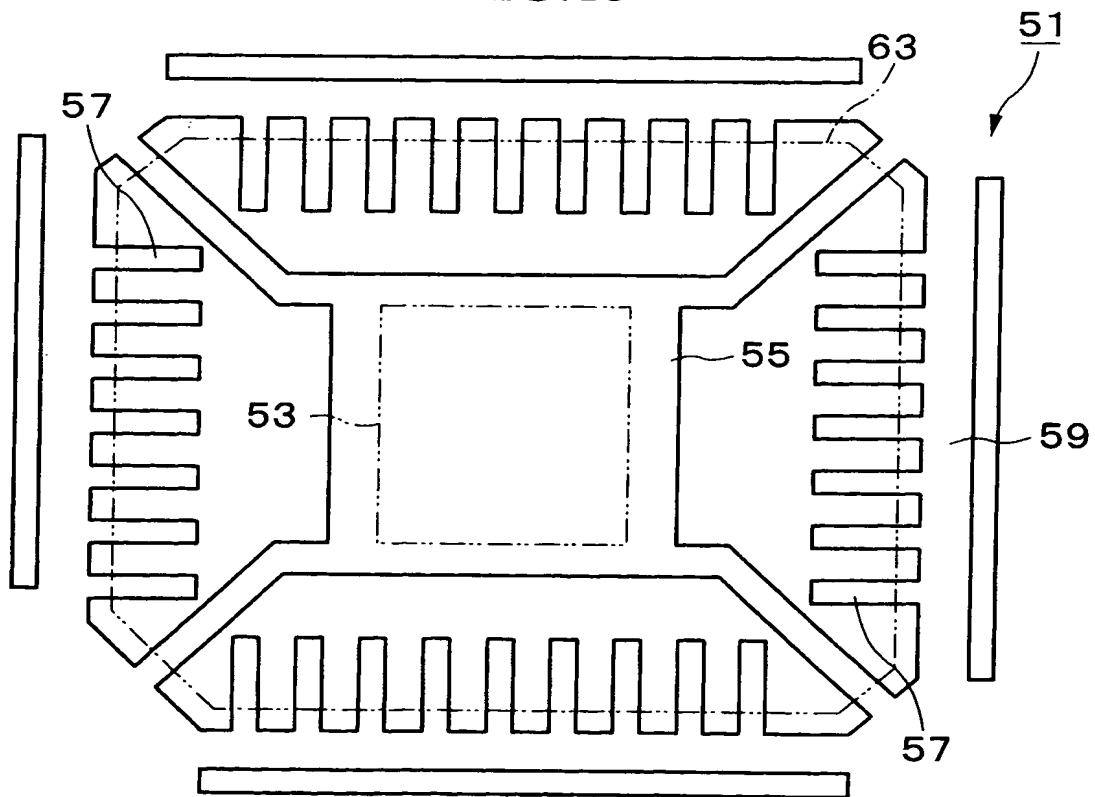


FIG.14

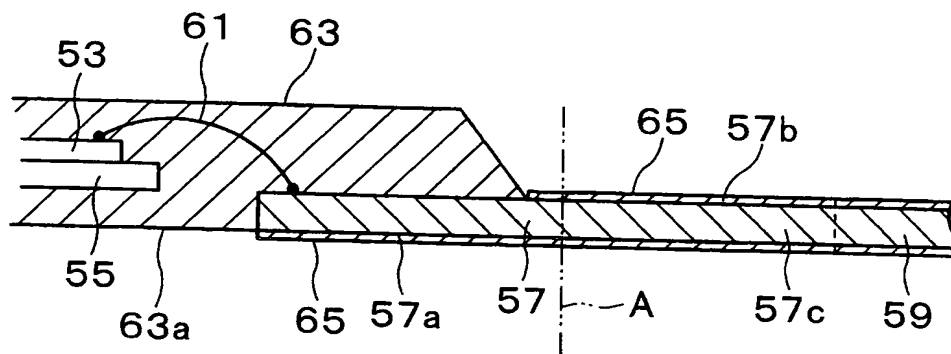


FIG.15

